

### **Boost chopper MOSFET Power Module**

### $V_{DSS} = 100V$ $R_{DSon} = 2.25m\Omega \text{ typ}$ @ Tj = 25°C $I_D = 495A$ (a) $Tc = 25^{\circ}C$

#### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### Features

- Power MOS V® MOSFETs

  - $\begin{array}{l} Low \; R_{DSon} \\ Low \; input \; and \; Miller \; capacitance \end{array}$
  - Low gate charge
  - Avalanche energy rated
  - Very rugged \_
- Kelvin source for easy drive
  - Very low stray inductance
  - Symmetrical design
    - M5 power connectors
- High level of integration •

#### **Benefits**

Outstanding performance at high frequency operation

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- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- **RoHS** Compliant

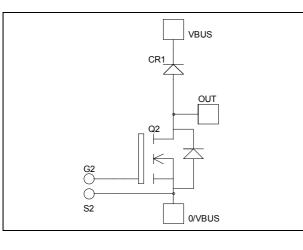
### Absolute maximum ratings

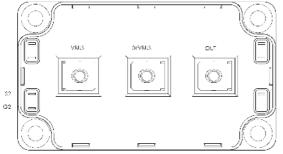
Symbol	Parameter		Max ratings	Unit
V <sub>DSS</sub>	Drain - Source Breakdown Voltage		100	V
I <sub>D</sub>	Continuous Drain Current $T_c = 25^{\circ}C$		495	
		$T_c = 80^{\circ}C$	370	А
I <sub>DM</sub>	Pulsed Drain current	1900		
V <sub>GS</sub>	Gate - Source Voltage		$\pm 30$	V
R <sub>DSon</sub>	Drain - Source ON Resistance		2.5	mΩ
P <sub>D</sub>	Maximum Power Dissipation $T_c = 25^{\circ}C$		1250	W
I <sub>AR</sub>	Avalanche current (repetitive and non repetitive)		100	А
EAR	Repetitive Avalanche Energy		50	mJ
E <sub>AS</sub>	Single Pulse Avalanche Energy		3000	ШJ

🕉 🚓 UTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

#### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 100V$ $T_j = 25^{\circ}C$			400	μA
		$V_{GS} = 0V, V_{DS} = 80V$ $T_j = 125^{\circ}C$			2000	
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 200A$		2.25	2.5	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10 \text{mA}$	2		4	V
I <sub>GSS</sub>	Gate – Source Leakage Current	$V_{GS} = \pm 30 V, V_{DS} = 0V$			±400	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	Input Capacitance	$V_{GS} = 0V$		40		
C <sub>oss</sub>	Output Capacitance	$V_{\rm DS} = 25 V$		15.7		nF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1MHz		5.9		
Qg	Total gate Charge	$V_{GS} = 10V$		1360		
Q <sub>gs</sub>	Gate – Source Charge	$V_{Bus} = 50V$		240		nC
$Q_{gd}$	Gate – Drain Charge	$I_{\rm D} = 400 {\rm A}$		720		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive switching @ 125°C		160		
Tr	Rise Time	$V_{GS} = 15V$ $V_{Bus} = 66V$		240		<b>n</b> c
T <sub>d(off)</sub>	Turn-off Delay Time	$I_{\rm D} = 400 \text{A}$		500		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 1.25\Omega$		160		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		2.2		mJ
E <sub>off</sub>	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 400A, R_G = 1.25\Omega$		2.41		IIIJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		2.43		
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 400A, R_G = 1.25\Omega$		2.56		mJ

### Chopper diode ratings and characteristics

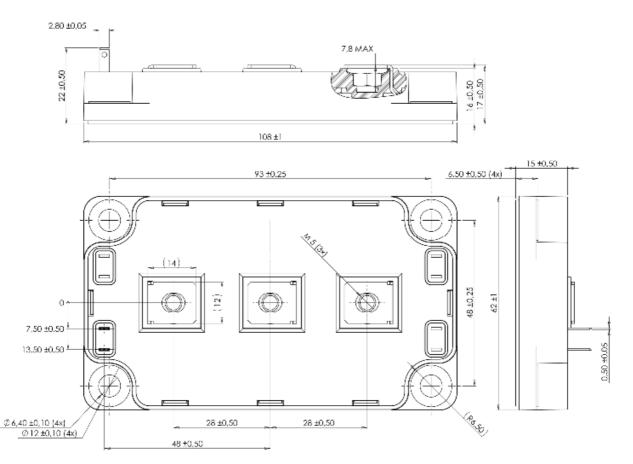
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			200			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =200V	$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$			750 1000	μΑ
I <sub>F</sub>	DC Forward Current		$Tc = 80^{\circ}C$		400		А
	Diode Forward Voltage	$I_F = 400A$			1		
V <sub>F</sub>		$I_F = 800A$			1.4		V
		$I_{\rm F} = 400 {\rm A}$	$T_{i} = 125^{\circ}C$		0.9		
t <sub>rr</sub>	Reverse Recovery Time	1 400 4	$T_j = 25^{\circ}C$		60		ns
чп		$I_{\rm F} = 400 {\rm A}$ $V_{\rm R} = 133 {\rm V}$	$T_{i} = 125^{\circ}C$		110		115
Q <sub>rr</sub>	Reverse Recovery Charge	$di/dt = 800 \text{A}/\mu \text{s}$	$T_j = 25^{\circ}C$		800		nC
			$T_{j} = 125^{\circ}C$		3360		iic



### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
<b>P</b>	Junction to Case Thermal Resistance		Transistor			0.1	°C/W
R <sub>thJC</sub>			Diode			0.14	C/ W
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		150	
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminal	s M5	2		3.5	19.111
Wt	Package Weight					300	g

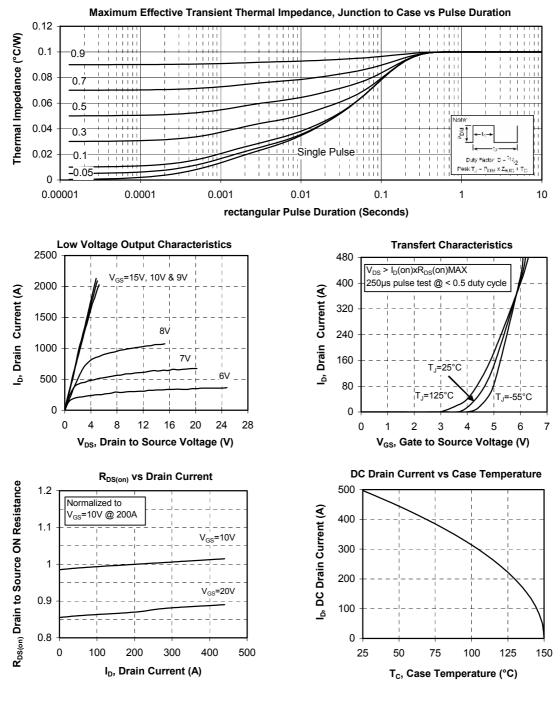
#### SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

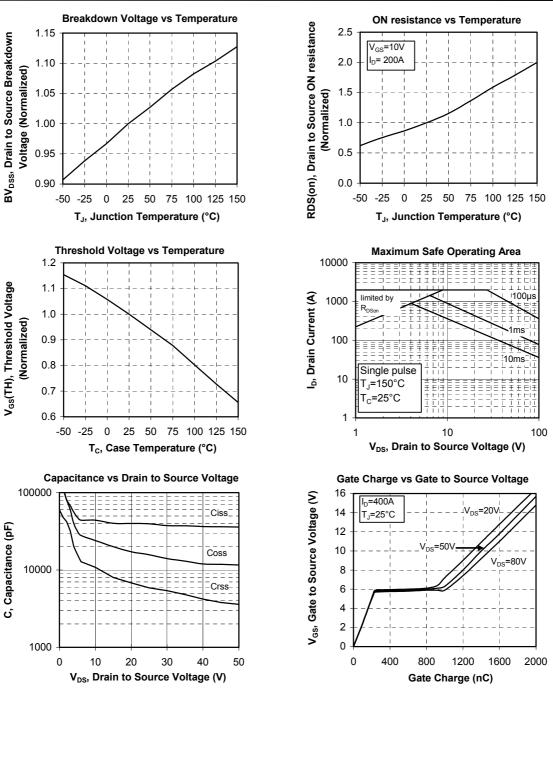


#### **Typical Performance Curve**



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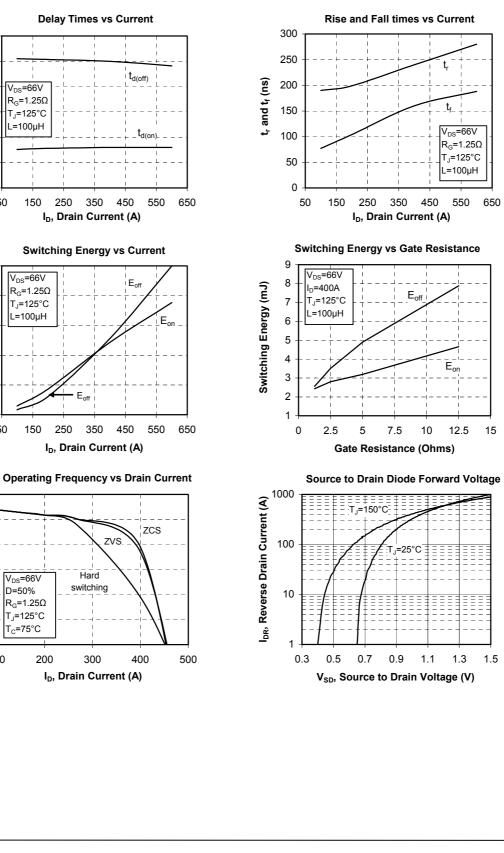


Frequency (kHz)

Eon and Eoff (mJ)

t<sub>d(on)</sub> and t<sub>d(off)</sub> (ns)

## APTM10DAM02G





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